

Jaeyi Chun

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

253
citations

1307594

7
h-index

1588992

8
g-index

11
all docs

11
docs citations

11
times ranked

455
citing authors

#	ARTICLE	IF	CITATIONS
1	Transfer of GaN LEDs From Sapphire to Flexible Substrates by Laser Lift-Off and Contact Printing. IEEE Photonics Technology Letters, 2012, 24, 2115-2118.	2.5	121
2	High-Performance Photoconductivity and Electrical Transport of ZnO/ZnS Core/Shell Nanowires for Multifunctional Nanodevice Applications. ACS Applied Materials & Interfaces, 2014, 6, 6170-6176.	8.0	41
3	Interferometric imaging using Si ₃ N ₄ photonic integrated circuits for a SPIDER imager. Optics Express, 2018, 26, 12801.	3.4	36
4	Vertically Stacked Color Tunable Light-Emitting Diodes Fabricated Using Wafer Bonding and Transfer Printing. ACS Applied Materials & Interfaces, 2014, 6, 19482-19487.	8.0	22
5	Titanium oxide nanotube arrays for high light extraction efficiency of GaN-based vertical light-emitting diodes. Nanoscale, 2016, 8, 10138-10144.	5.6	12
6	Enhanced optical output power of InGaN/GaN light-emitting diodes grown on a silicon (111) substrate with a nanoporous GaN layer. Optics Express, 2016, 24, 4391.	3.4	11
7	Schottky Junction Vertical Channel GaN Static Induction Transistor with a Sub-Micrometer Fin Width. Advanced Electronic Materials, 2019, 5, 1800689.	5.1	7
8	Fabrication of glass-free photoelectrodes for dye-sensitized solar cells (DSSCs) by transfer method using ZnO nanorods sacrificial layer. Materials Letters, 2014, 132, 27-30.	2.6	3
9	Si ₃ N ₄ photonic integrated circuit for multi-baseline interferometric imaging. , 2017, , .		0
10	A Study on the First-Derivative Output Properties of GaN Static Induction Transistor with Submicrometer Fin Width. Physica Status Solidi (B): Basic Research, 2020, 257, 1900545.	1.5	0